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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/711,383	09/15/2004	Timothy H. Daubenspeck	BUR920040151US1	5382
30449 7:	590 04/19/2006		EXAMINER	
SCHMEISER, OLSEN & WATTS			DANG, TRUNG Q	
22 CENTURY SUITE 302	HILL DRIVE		ART UNIT PAPER NUMBER	
LATHAM, NY	7 12110		2823	

DATE MAILED: 04/19/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

			<u></u>
	Application No.	Applicant(s)	
	10/711,383	DAUBENSPECK ET A	L.
Office Action Summary	Examiner	Art Unit	
	Trung Dang	2823	
The MAILING DATE of this communication Period for Reply	appears on the cover sheet w	ith the correspondence addres	s
A SHORTENED STATUTORY PERIOD FOR RE WHICHEVER IS LONGER, FROM THE MAILING - Extensions of time may be available under the provisions of 37 CFF after SIX (6) MONTHS from the mailing date of this communication If NO period for reply is specified above, the maximum statutory per - Failure to reply within the set or extended period for reply will, by state Any reply received by the Office later than three months after the mearned patent term adjustment. See 37 CFR 1.704(b).	B DATE OF THIS COMMUNI R 1.136(a). In no event, however, may a riod will apply and will expire SIX (6) MO atute, cause the application to become A	CATION. reply be timely filed NTHS from the mailing date of this commun BANDONED (35 U.S.C. § 133).	
Status			
1) Responsive to communication(s) filed on 0	7 March 2006.		
	his action is non-final.		
3) Since this application is in condition for allo	wance except for formal mat	ters, prosecution as to the me	rits is
closed in accordance with the practice under	er <i>Ex parte Quayle</i> , 1935 C.I	D. 11, 453 O.G. 213.	
Disposition of Claims			
4) Claim(s) 1-20 is/are pending in the applicat	ion.		
4a) Of the above claim(s) <u>15-20</u> is/are without			
5)⊠ Claim(s) <u>6, 8-14</u> is/are allowed.			
6)⊠ Claim(s) <u>1,2,4 and 7</u> is/are rejected.			
7)⊠ Claim(s) <u>3 and 5</u> is/are objected to.			
8) Claim(s) are subject to restriction an	d/or election requirement.		
Application Papers			
9) The specification is objected to by the Exam	niner.		
10) The drawing(s) filed on is/are: a)		by the Examiner.	
Applicant may not request that any objection to			
Replacement drawing sheet(s) including the cor			.121(d).
11) The oath or declaration is objected to by the			
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for fore a) All b) Some * c) None of:	eign priority under 35 U.S.C.	§ 119(a)-(d) or (f).	
1. Certified copies of the priority docum	ents have been received.	•	
2. Certified copies of the priority docum	ents have been received in	Application No	
3. Copies of the certified copies of the p	priority documents have been	n received in this National Stag	ge .
application from the International Bu	reau (PCT Rule 17.2(a)).		
* See the attached detailed Office action for a	list of the certified copies no	t received.	
Attachment(s)			
1) Notice of References Cited (PTO-892)		Summary (PTO-413)	
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	_	(s)/Mail Date Informal Patent Application (PTO-152	2)
 Information Disclosure Statement(s) (PTO-1449 or PTO/SB Paper No(s)/Mail Date 	6) Other:		•

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DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 2. Claims 1 and 7 are rejected under 35 U.S.C. 102(e) as being anticipated by Takao of record.

The rejection is maintained as of record and repeated herein.

With reference to Figs. 5-8B, the reference teaches the claimed invention in that it discloses method for chip separation comprising the steps of:

- (a) providing a semiconductor substrate 10,
- (b) forming first and second device regions 10A (Fig. 8B) in and at top of the semiconductor substrate 10, wherein the first and second device regions are separated by a semiconductor border region of the semiconductor substrate 10 (Fig. 8A wherein the dicing line region corresponds to the claimed semiconductor border region)
- (c) forming N interconnect layers, in turn, including a bottom copper layer 21 and a top barrier metal layer (not shown in Fig. 5) directly above the

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block;

semiconductor border region and the first and second device regions 10A using photoresist layer 19 as a mask (Fig. 5 and paras. [0061]-[0063]), wherein N is a positive integer greater than one, wherein each layer of the N interconnect layers comprises an etchable portion (photoresist block 19 reads on this limitation because the photoresist block 19 connects the left and right portions of the bottom copper layer 21 and the top barrier layer. That is, the photoresist block 19 is considered as an integral part of the two metal layers) directly above the semiconductor border region, and wherein the etchable portions of the N interconnect layers form a continuous etchable block directly above the semiconductor border region, and wherein the entire continuous etchable block 19 comprises essentially a same material (i.e., photoresist material) throughout the entire continuous etchable

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- (d) removing the continuous etchable block 19 by etching (Fig. 7 and para. [0064];
- (e) cutting with a laser through the semiconductor border region via an empty space of the removed continuous etchable block (Fig. 8B and para. [0066]).
- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the

invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

4. Claims 2 and 4 are rejected under 35 U.S.C. 103(a) as being unpatentable over Takao as above in view of Chae et al. (US 6,958,312).

The rejection is maintained as of record and repeated herein.

Takao teaches a method for chip separation as described above.

Takao differs from the claims in not disclosing that the photoresist block is removed by wet etching.

Chae recognizes that it is known to remove a photoresist mask using a wet etching process. However, the conventional solvents causes metal line formed of copper easily corroded (col. 2, lines 15-20). Accordingly, Chae teaches a solvent composition which is used to remove the photoresist material without corroding copper metal line (col. 2, lines 37-40; col. 3, lines 64-67).

It would have been obvious to one of ordinary skill in the art to modify Takao's teaching by removing the photoresist block 19 using a wet etching process with the solvent composition taught by Chae because the use of such solvent would prevent corrosion of the copper interconnect layer 21.

Allowable Subject Matter

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2. Claims 3 and 5 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

- 3. Claims 6, 8-14 are allowed.
- 4. The following is a statement of reasons for the indication of allowable subject matter:

Claims 3 and 5 are indicated allowable over prior art of record because the prior art does not teach or suggest the subject matter as claimed which includes the limitation regarding the continuous etchable block comprises cooper as recited in claim 3 or the back-side grinding and applying a dicing tape steps as recited in claim 5.

Independent claims 6 and 8 are allowed over prior art of record for the same reasons noted in previous Office action.

Amended independent claim 12 is allowed over prior art of record because the prior art does not teach or suggest the subject matter as claimed which includes the limitations regarding a deep filled trench in and at top of the semiconductor substrate and the entire continuous etchable block comprises essentially a same material throughout the entire continuous etchable block.

Response to Arguments

5. Applicant's arguments filed 2/8/06 have been fully considered but they are not persuasive.

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In page 15 of the Remarks, applicants argue that "More specifically, if layers 18, 19 and 30 in Fig. 5 of Takao were considered interconnect layers for the purpose of anticipating claim 1, their etchable portions would not form a continuous etchable block which comprises essentially a same material throughout the entire continuous etchable block as claimed in claim 1. This is because the layers 18, 19 and 30 comprises different

materials (paragraphs 59, 60 and 61), Therefore, claim 1 is not anticipated by Takao."

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The Examiner disagrees. As pointed out in the rejection, a bottom copper layer 21 and a top barrier metal layer (not shown in Fig. 5 but disclosed in para.[0063]) anticipates the claimed N interconnect layers, wherein each layer of the N interconnect layers comprises an etchable portion (photoresist block 19 reads on this limitation because the photoresist block 19 connects the left and right portions of the bottom copper layer 21 and the top barrier layer. That is, the photoresist block 19 is considered as an integral part of the two metal layers). Here, the photoresist block 19 corresponds to the claimed etchable block, and the etchable block 19 comprises essentially a same material, i.e. photoresist material, throughout the entire continuous etchable block.

6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Trung Dang whose telephone number is 571-272-1857. The examiner can normally be reached on Mon-Friday 9:30am-6:00pm.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith can be reached on 571-272-1907. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Trung Dang Primary Examiner Art Unit 2823

04/17/06